CNB2301 (ON2270)

Reflective photosensor

Non-contact point SW, object sensing

Overview

CNB2301 is a small, thin reflective photosensor consisting of a high efficiency GaAs infrared light emitting diode which is integrated with a high sensitivity Darlington phototransistor used as the photo detector in a single resin package.

■ Features

- Ultraminiature: $2.7 \text{ mm} \times 3.4 \text{ mm}$
- Visible light cutoff resin is used
- High current-transfer ratio

Applications

- Detection of paper, film and cloth Detection of position and edge
- Liquid level sensor
- Detection of rotary positioning
- Start, end mark detection of magnetic tape

■ Absolute Maximum Ratings $T_a = 25$ °C

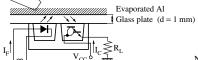
	Parameter	Symbol	Rating	Unit			
Input (Light	Reverse voltage	V _R	3	V			
emitting diode)	Forward current	I_F	50	mA (
	Power dissipation	P_{D}	75	mW			
Output (Photo	Collector-emitter voltage	V _{CEO}	20	/X			
transistor)	(Base open)		/				
	Emitter-collector voltage	V _{ECO}	5 //	V			
	(Base open)						
	Collector current	I_C	30/ ^	mA			
	Collector power dissipation	P_{C}	75	mW			
Temperature	Operating ambient temperature	U OPA	+25 to +88	°C			
	Storage temperature	T _{stx}	-30 to +100	°C			

■ Electrical-Optical Characteristics $T_a = 25$ °C ± 3 °C

	Parameter	Symbol		Conditions	Min	Тур	Max	Unit
Input	Forward voltage	V _F	IR	50 mA		1.3	1.5	V
characteristics	Reverse current	I_R	V _R	= 3 V		0.01	10.00	μΑ
	Terminal capacitance	C_t	VR	= 0 V, f = 1 MHz		30		pF
Output	Collector-emitter cutoff current	$\sqrt{I_{CEO}}$	V _{CE}	$_{\rm E} = 10 \text{ V}$			1.0	μΑ
characteristics	(Base open)							
Transfer	Collector current N. 2	I_C	V_{CC}	= 5 V, I_F = 2 mA, R_L = 100 Ω , d = 1 mm	0.46		12.00	mA
characteristics	Dark current	I_D	V_{CC}	$_{\rm C} = 5 \text{ V}, I_{\rm F} = 2 \text{ mA}, R_{\rm L} = 100 \Omega$			2.0	μΑ
	Collector-emitter saturation voltage	V _{CE(sat)}	I _F =	$5 \text{ mA}, I_{\text{C}} = 0.5 \text{ mA}$			1.5	V
	Rise time	t _r	V _{CC}	$_{\rm C} = 10 \text{ V}, I_{\rm C} = 1 \text{ mA}, R_{\rm L} = 100 \Omega$		150		μs
	Falltime	$t_{\rm f}$				150		μs

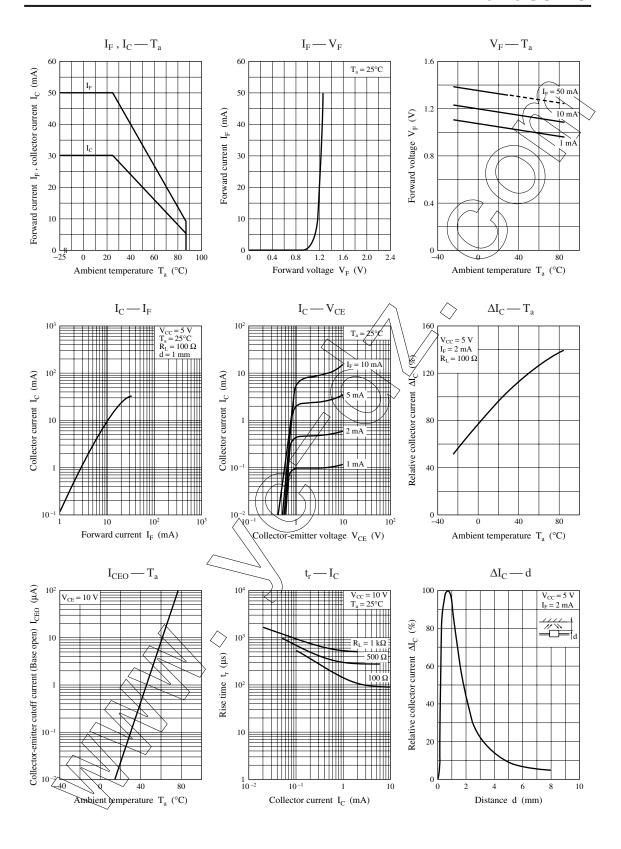
Note) 1. Input and output are handled electrically.

2. This product is not designed to withstand radiation



Rank	Q	R	S
I_{C} (mA)	0.46 to 1.75	1.30 to 4.95	3.15 to 12.00
Color	Pink	Black	Blue

Note) The part number in the parenthesis shows conventional part number.



Caution for Safety

⚠ DANGER

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

Request for your special attention and precautions in using the technical information and semiconductors described in this material

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